

Title (en)

GATE DIELECTRIC FOR A THIN FILM FIELD EFFECT TRANSISTOR

Publication

EP 0408653 A4 19911016 (EN)

Application

EP 89904998 A 19890314

Priority

US 17626488 A 19880331

Abstract (en)

[origin: WO8909494A1] A thin film field effect transistor utilizes a double-layer of dielectric material with a first layer (14) of an insulating crystalline or amorphous material and a second layer (16) of silicon nitride. The first layer has a high dielectric constant and the second layer eliminates pinholes which could occur in the first layer.

IPC 1-7

H01L 27/12; H01L 29/78; H01L 29/34

IPC 8 full level

H01L 29/49 (2006.01)

CPC (source: EP)

H01L 29/4908 (2013.01)

Citation (search report)

- [X] DE 3539794 A1 19860522 - SHARP KK [JP]
- [X] DE 3306535 A1 19830915 - SHARP KK [JP]
- [A] EP 0027184 A1 19810422 - ROCKWELL INTERNATIONAL CORP [US]
- [A] WO 8404418 A1 19841108 - NCR CO [US]
- [Y] PATENT ABSTRACTS OF JAPAN vol. 9, no. 263 (E-351)(1986) 19 October 1985, & JP-A-60 109285 (SEIKO DENSHI KOGYO K.K.) 14 June 1985,
- [Y] IEEE TRANSACTIONS ON ELECTRON DEVICES. vol. ED-34, no. 5, May 1987, NEW YORK US pages 1079 - 1083; MARK S. RODDER et al: "Hot-Carrier Effects in Hydrogen-Passivated p-Channel Polycrystalline-Si MOSFET's"
- See references of WO 8909494A1

Designated contracting state (EPC)

AT BE CH DE FR GB IT LI LU NL SE

DOCDB simple family (publication)

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